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RRAM

	Document ID	Issue Date	Pages	Title	Category	Current Xref
1	<input type="checkbox"/> <input type="checkbox"/> US 20050054119 A1	20050310	15	Buffered layer memory cell	438/3	365/158; 438/197
2	<input type="checkbox"/> <input type="checkbox"/> US 20050040482 A1	20050224	19	EPIT device and semiconductor devices utilizing the same	257/411	
3	<input type="checkbox"/> <input type="checkbox"/> US 20050024967 A1	20050303	15	Semiconductor memory device	365/207	
4	<input type="checkbox"/> <input type="checkbox"/> US 20040264244 A1	20041230	36	Nonvolatile semiconductor memory device and control method thereof	365/180	
5	<input type="checkbox"/> <input type="checkbox"/> US 20040257384 A1	20041223	37	Nonvolatile semiconductor memory device, and programming method and erasing method thereof	365/158	
6	<input type="checkbox"/> <input type="checkbox"/> US 20040256697 A1	20041223	12	[RESISTANCE RANDOM ACCESS MEMORY AND METHOD FOR FABRICATING THE SAME]	257/578	
7	<input type="checkbox"/> <input type="checkbox"/> US 20040245547 A1	20041209	40	Ultra low-cost solid-state memory	257/200	
8	<input type="checkbox"/> <input type="checkbox"/> US 20040240273 A1	20041202	81	Nonvolatile semiconductor memory	365/185.33	
9	<input type="checkbox"/> <input type="checkbox"/> US 20040235309 A1	20041125	25	High-density SOI cross-point memory array and method for fabricating same	438/706	
10	<input type="checkbox"/> <input type="checkbox"/> US 20040235247 A1	20041125	10	Asymmetric crystalline structure memory cell	438/257	
11	<input type="checkbox"/> <input type="checkbox"/> US 20040204800 A1	20041014	12	Electronic control unit for a vehicle	701/1	